

TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SA1384

HIGH VOLTAGE CONTROL APPLICATIONS

PLASMA DISPLAY, NIXIE TUBE DRIVER APPLICATIONS

CATHODE RAY TUBE BRIGHTNESS CONTROL APPLICATIONS

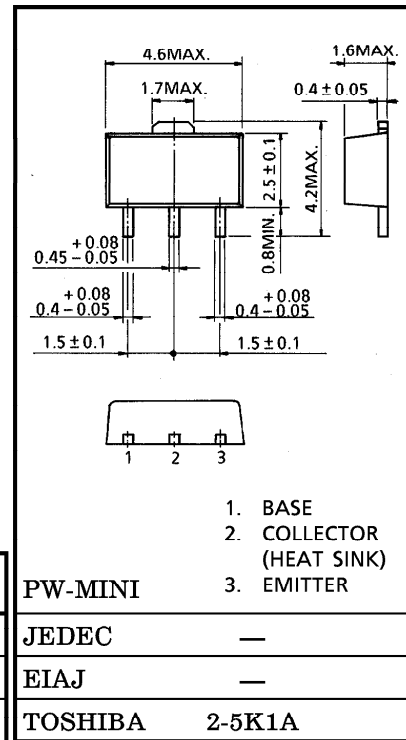
- High Voltage : $V_{CBO} = -300V$, $V_{CEO} = -300V$
- Low Saturation Voltage : $V_{CE(sat)} = -0.5V$ (Max.)
- Small Collector Output Capacitance : $C_{ob} = 6pF$ (Typ.)
- Complementary to 2SC3515
- Small Flat Package
- $P_C = 1 \sim 2W$ (Mounted Ceramic Substrate)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-8	V
Collector Current	I_C	-100	mA
Base Current	I_B	-20	mA
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation	P_C^*	1000	mW
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

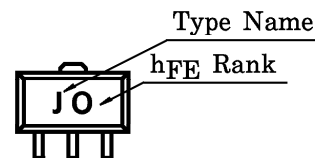
P_C^* : 2SA1384 mounted on ceramic substrate ($250mm^2 \times 0.8mm^t$)

Unit in mm



Weight : 0.05g

Marking



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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -300V, I_E = 0$	—	—	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -8V, I_C = 0$	—	—	-0.1	μA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-300	—	—	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-300	—	—	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -10V, I_C = -20mA$	30	—	150	
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -1mA$	20	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -20mA, I_B = -2mA$	—	—	-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -20mA, I_B = -2mA$	—	—	-1.0	V
Transition Frequency	f_T	$V_{CE} = -10V, I_C = -20mA$	50	70	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -20V, I_E = 0, f = 1MHz$	—	6	8	pF

Note : $h_{FE(1)}$ Classification R : 30~90 O : 50~150

